

# Lecture 3 - Ionic Conductivity

# Lecture summary

- Recap of defect types
- Ionic conductivity
- Conduction mechanisms
- Ionic migration paths
- Energetics of conduction

# Defect recap

# Defect recap results

**wooclap**

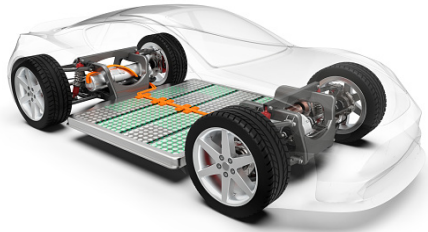
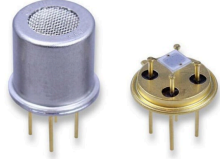
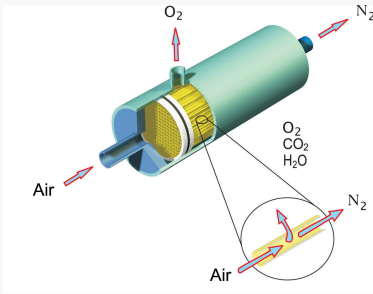

Quiz results will be available here  
after the lecture

# Conductivity

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- Most ionic solids are electrically insulating/semiconducting (localised electrons)
- Ionic conductors are important!

	
Batteries ( <a href="#">Lecture 4</a> )	Sensors
	
Separation Membranes	Fuel Cells ( <a href="#">Lecture 6</a> )

# Origin of ionic conduction

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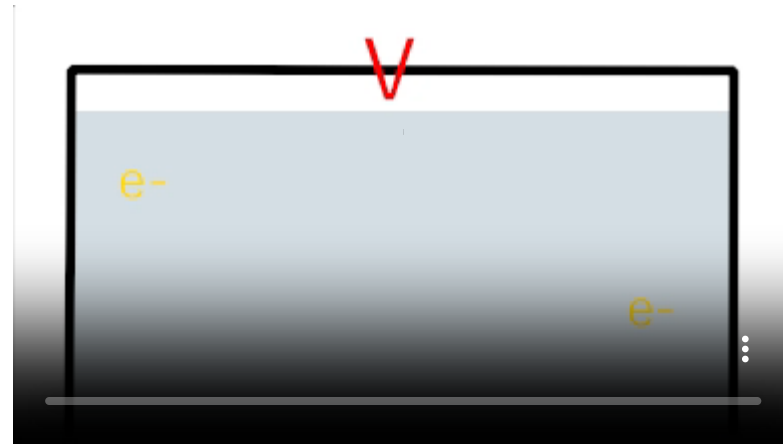


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- In ionic solids, conductivity covers  $10^{-16} \text{ S m}^{-1} - 10^3 \text{ S m}^{-1}$ 
  - most solids are limited to around  $10^{-2} \text{ S m}^{-1}$
  - Liquid electrolytes typically  $10^{-1} - 10^3 \text{ S m}^{-1}$

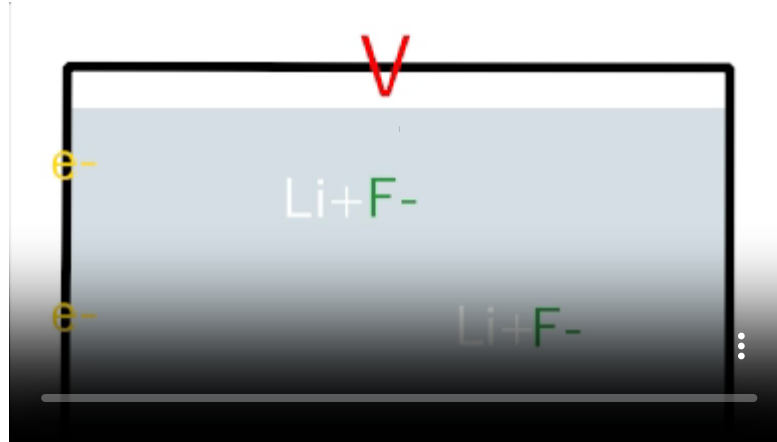
# Measuring Conductivity

- For electronic conductors, this is simple:
  - Apply a voltage ( $V$ ) and measure the resulting current ( $I$ )
  - Resistance (in  $\Omega$ ) is found through Ohm's law;  $V = IR$
  - Resistivity (in  $\Omega \text{ cm}$ ) of the material calculated from geometry
- Resistivity  $\rho$  (in  $\Omega \text{ cm}$ ) =  $\frac{1}{\text{Conductivity } \sigma \text{ (in } \text{S cm}^{-1}\text{)}}$



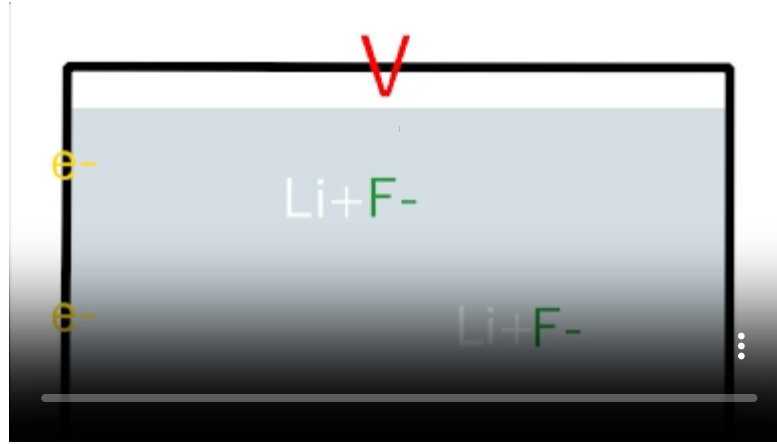
# Measuring Ionic Conductivity

- Ions cannot flow round a circuit, so current drops with a constant applied voltage

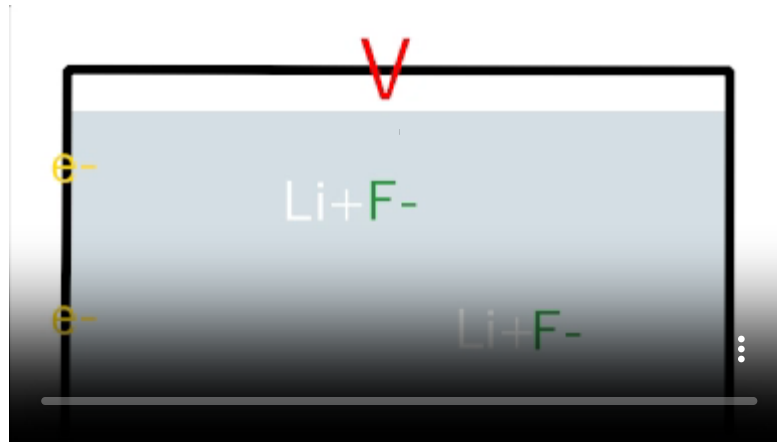


# Measuring Ionic Conductivity

- Ions cannot flow round a circuit, so current drops with a constant applied voltage



- Instead, we use an alternating voltage - this is called Impedance spectroscopy (see [lecture 5](#))



# Ion migration mechanisms

Three 'main' mechanisms of ionic migration

## 1. Vacancy mechanism

Vacancies move throughout the lattice (atoms move into vacancy)



## 2. Interstitial mechanism

Ions hop between interstitial sites



### 3. Interstitialcy (knock-on) mechanism

Interstitial ions 'push' into a neighbouring site



# Vacancy, Interstitial or Interstitialcy?



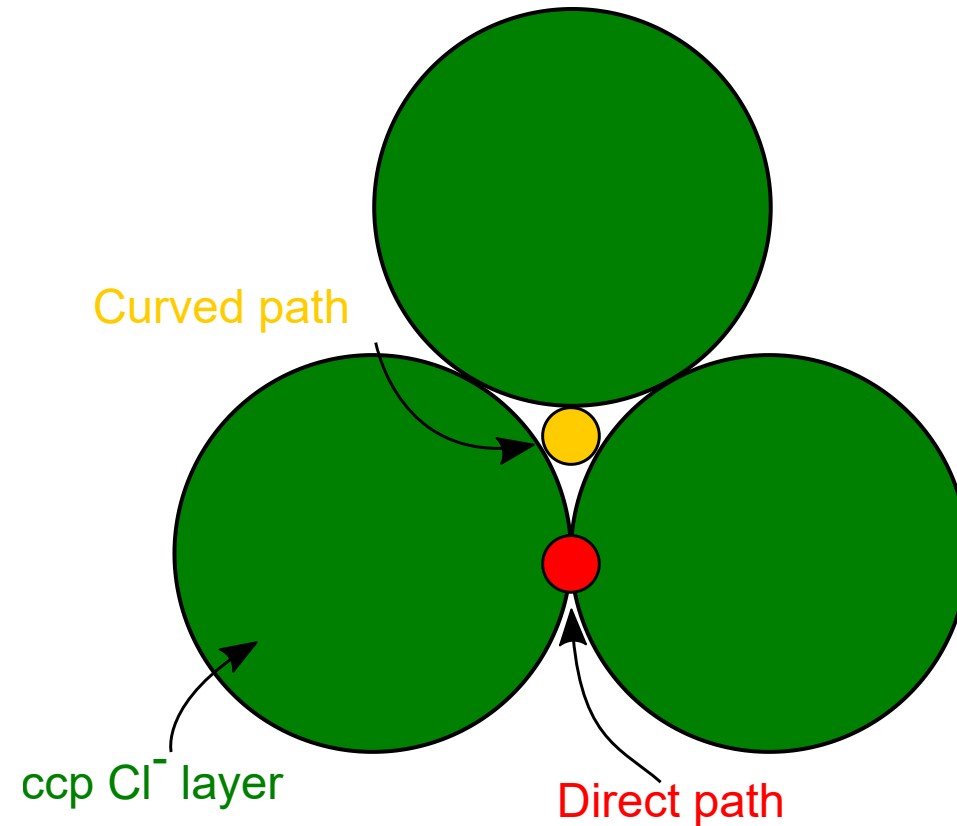
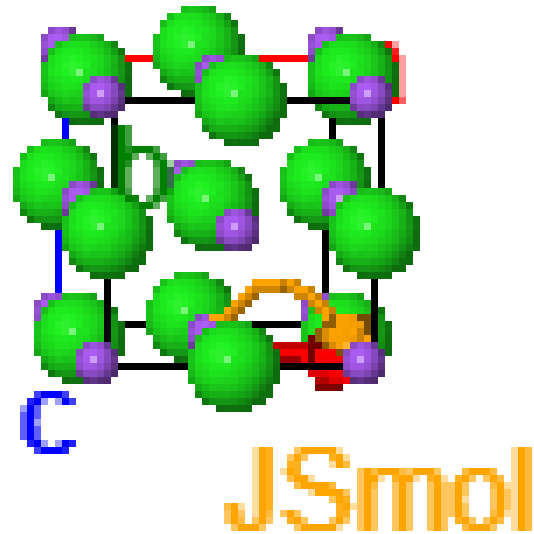
# Suggestions

**wooclap**

Quiz results will be available here  
after the lecture

# Migration paths

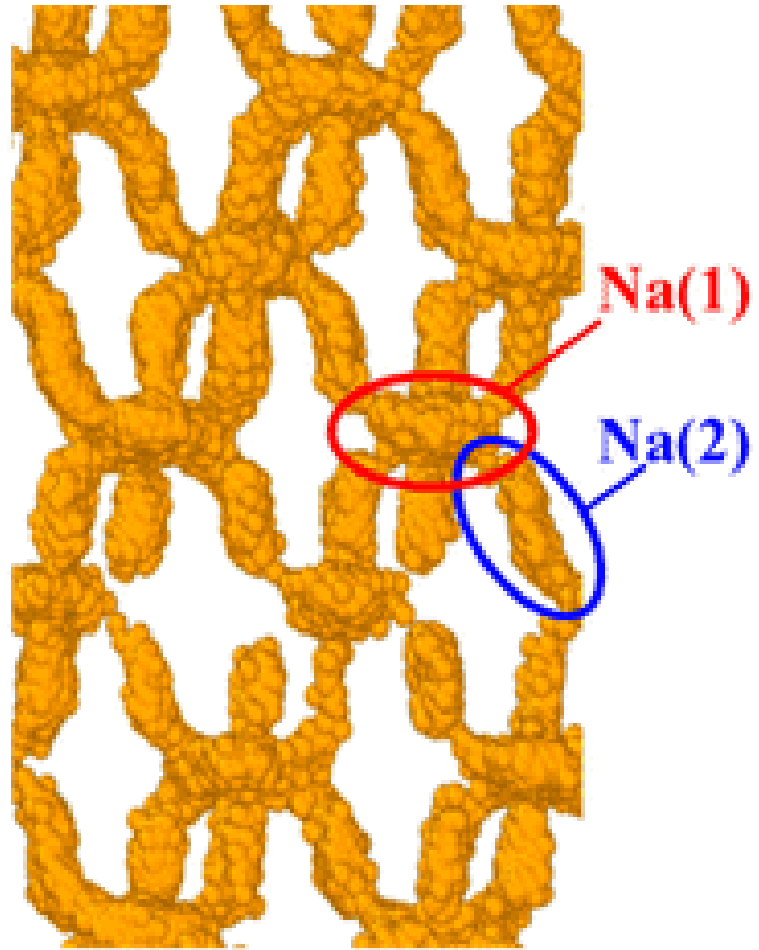
Ion paths are rarely **direct**, but will take the **lowest energy route**.



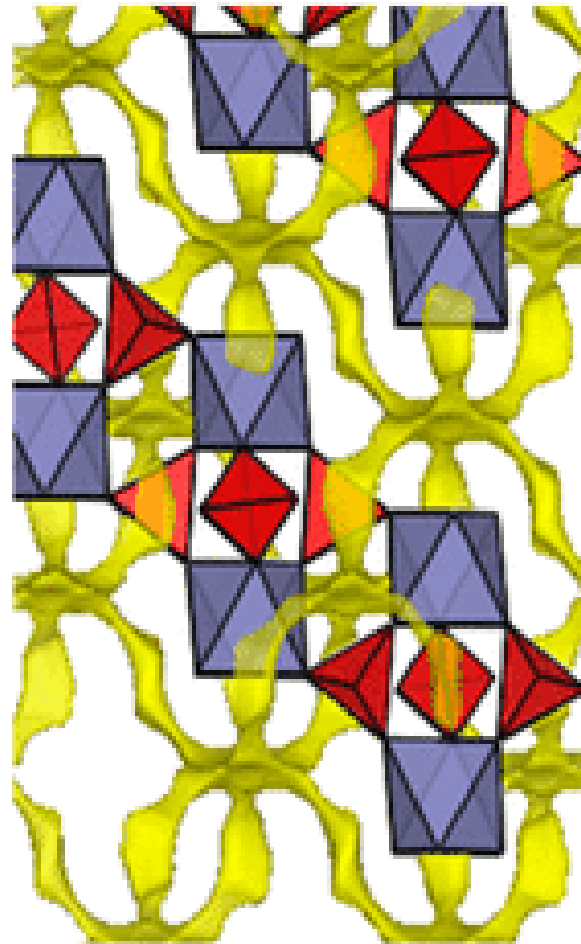
# Pathways can be complex

- Migration pathways can be calculated and/or experimentally determined

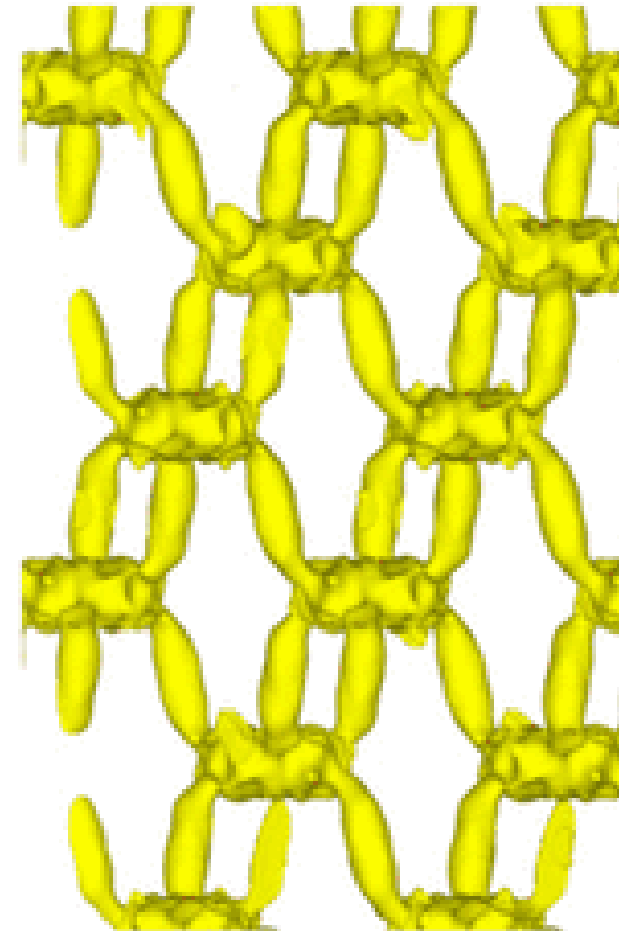
e.g. **NASICON**  $\text{Na}^+$  conductor,  $\text{Na}_3\text{Zr}_2(\text{SiO}_4)_2(\text{PO}_4)$ :



**MD density plot**



**BVEL**



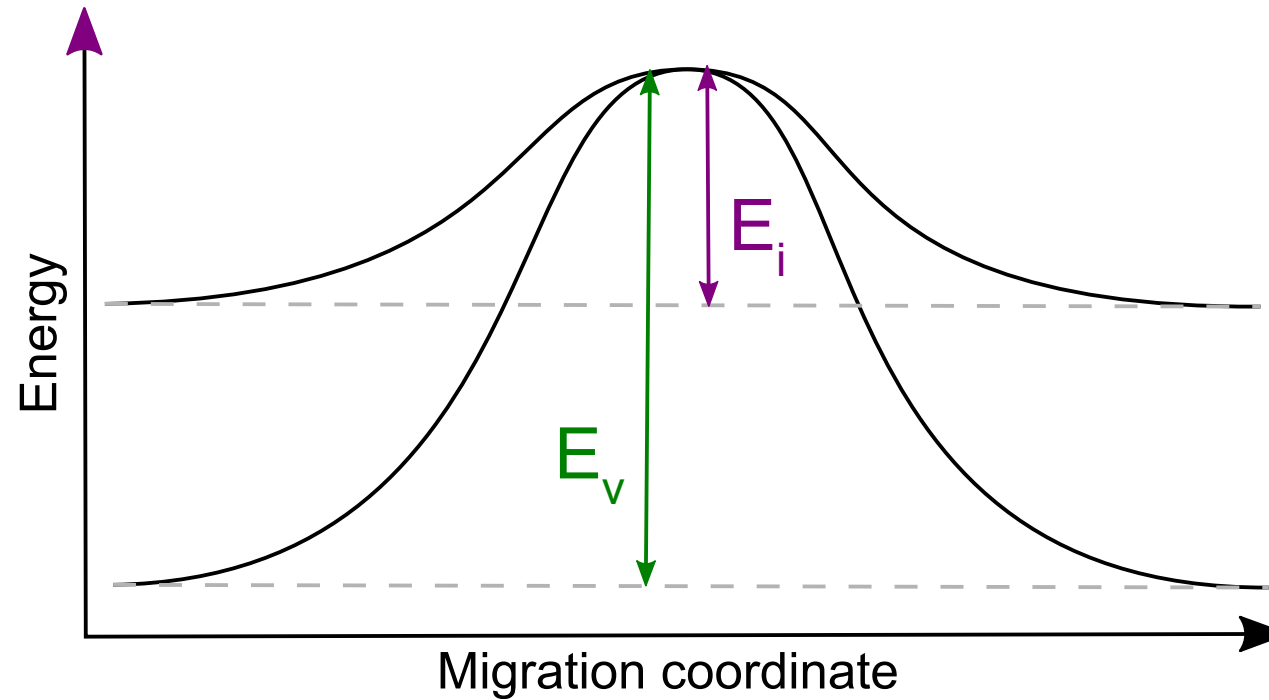
**MEM/Rietveld**

# Migration energetics

- Defect mobility ( $\mu$ ) is a thermally-activated process:

$$\mu = \mu_0 \exp\left(-\frac{E_a}{RT}\right)$$

- interstitial sites are higher energy than vacancies, so will be more mobile.



# Variation with temperature

As  $\sigma = nq\mu$  and  $\mu$  is thermally-activated,

$$\begin{aligned}\sigma &= nq\mu_0 \exp\left(-\frac{E_a}{RT}\right) \\ &= A \exp\left(-\frac{E_a}{RT}\right)\end{aligned}$$

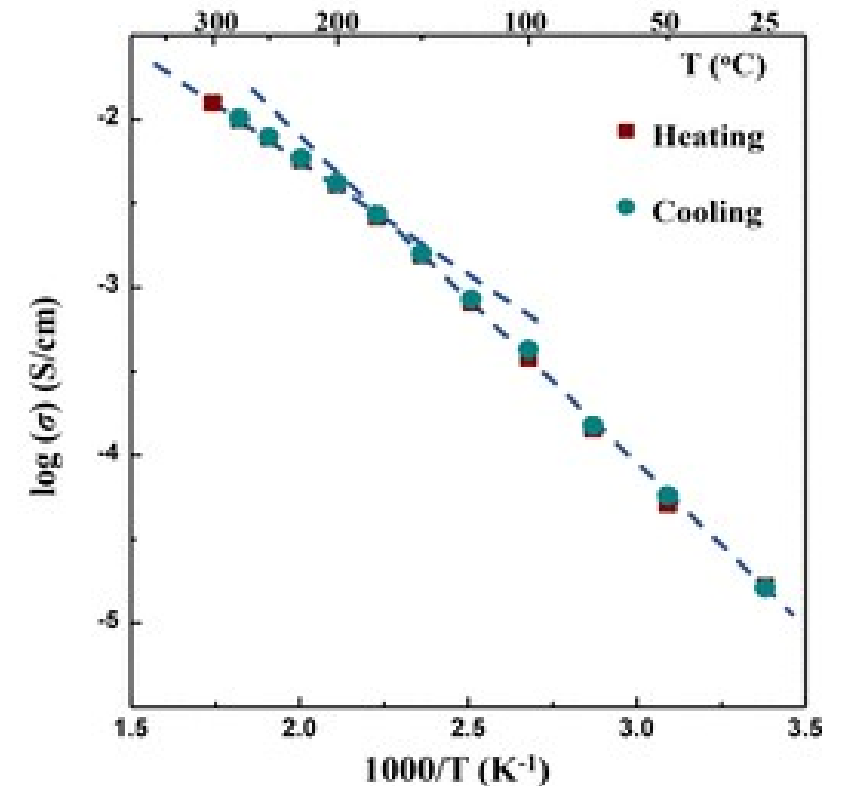
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Plotting  $\ln \sigma$  vs.  $\frac{1}{T}$  should give a straight line

- more commonly we plot  $\log_{10} \sigma$  vs.  $\frac{1000}{T}$  for high temperature measurements
- gradient is  $\frac{-E_a}{R}$  (or  $\frac{-E_a}{2303R}$  using base 10).



# Lecture recap

- Defects can give rise to ionic conduction
  - Occurs by three main mechanisms:
    - Vacancy hopping
    - Interstitial hopping
    - interstitialcy (knock-on) cooperation
- Ionic conductivity is thermally-activated
  - shows Arrhenius-like behaviour
- Different defects have different conduction energetics
  - Pathways can sometimes be determined experimentally

# Feedback



